



N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI®

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _C = +25°C	
30V	$8.5 m\Omega @ V_{GS} = 10V$	30A	
30 V	$10.5 \text{m}\Omega @ V_{GS} = 4.5 \text{V}$	25A	

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

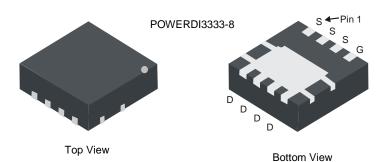
- Backlighting
- DC-DC Converters
- Power Management Functions

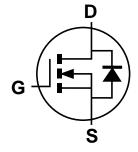
Features

- Low R_{DS(ON)} ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- 100% UIS (Avalanche) rated
- 100% Rg tested
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: POWERDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (@3)
- Weight: 0.072 grams (Approximate)





Equivalent Circuit

Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMN3010LFG-7	Standard	POWERDI3333-8	2,000/Tape & Reel
DMN3010LFG-13	Standard	POWERDI3333-8	3,000/Tape & Reel

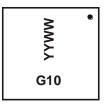
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Document number: DS36195 Rev. 7 - 2

PowerDI3333-8



G10 = Product Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 15 for 2015) WW = Week Code (01 – 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteris	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	30	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Dunin Comment (Note C) // 40)/	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	11 8.5	А
Continuous Drain Current (Note 6) V _{GS} = 10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	14 11	А
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	30 20	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%	I _{DM}	90	Α		
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	12.7	А		
Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	8.1	mJ		

Thermal Characteristics

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)		P_D	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	137	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t < 10s		90	°C/W
Total Power Dissipation (Note 6)		P_{D}	2.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	52	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t < 10s	$R_{\theta JA}$	35	°C/W
Total Power Dissipation (Note 6)	Tc = +25°C	P_D	26	W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	4.8	°C/W
Operating and Storage Temperature Range		T_{J}, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage		30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C		l	_	1	μA μA	V _{DS} = 30V, V _{GS} = 0V	
Zero Gate Voltage Drain Current T _J = +150°C (Note 9)	I _{DSS}	_	_	100			
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(th)}	1.0		2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D	1	6.5	8.5	mΩ	$V_{GS} = 10V, I_D = 18A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	l	8	10.5	11177	$V_{GS} = 4.5V, I_D = 16A$	
Diode Forward Voltage	V_{SD}		0.75	1.0	V	$V_{GS} = 0V$, $I_S = 1A$	
On State Drain Current (Note 9)	$I_{D(ON)}$	10	_	_	Α	$V_{DS} \leq 5V$, $V_{GS} = 4.5V$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	l	2,075	4,150		V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	1	190	380	pF		
Reverse Transfer Capacitance	C _{rss}	_	138	276		I = 1.0lvii iz	
Gate Resistance	Rg	ı	2.4	5	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	16.1	32			
Total Gate Charge (V _{GS} = 10V)	Qg	_	37	74	nC	15)/ 15)/ 1 100	
Gate-Source Charge	Q _{gs}	_	6.1	12	IIC	V _{DS} = 15V, I _D = 18A	
Gate-Drain Charge	Q_{gd}	_	5.9	12			
Turn-On Delay Time	t _{D(on)}		4.5	10		V _{DS} = 15V, V _{GS} = 10V,	
Turn-On Rise Time	t _r		19.6	35			
Turn-Off Delay Time	t _{D(off)}	-	31	50	ns	$R_L = 0.83\Omega$, $R_{GEN} = 3\Omega$,	
Turn-Off Fall Time	t _f	_	10.7	21			
Reverse Recovery Time	t _{rr}	-	13.7	27	ns	1 450 11/11 5000/-	
Reverse Recovery Charge	Q_{rr}	-	18.3	37	nC I _F =15A, di/dt=500A/µs		

Notes:

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.

7. UIS in production with L = 1mH, TJ = +25°C.

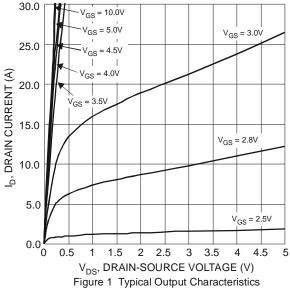
S. Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.

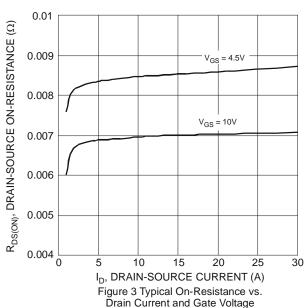
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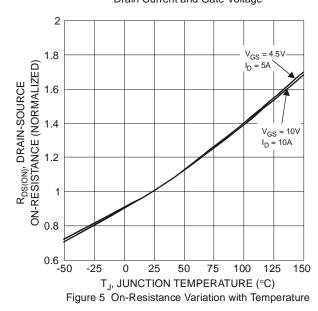
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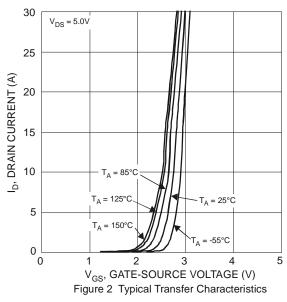
DMN3010LFG

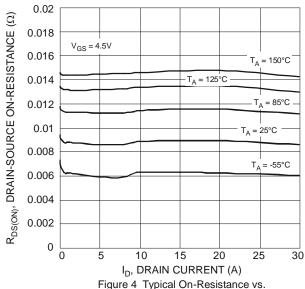












Drain Current and Temperature 0.02 $R_{DS(ON)}$, DRAIN-SOURCE ON-RESISTANCE (Ω) 0.018 0.016 $V_{GS} = 5.0V$ 0.014 $I_D = 5A$ 0.012 0.01 V_{GS} = 10V 0.008 I_D = 10A 0.006 0.004 0.002 -25 25 50 75 100 125 -50 T_J , JUNCTION TEMPERATURE (°C)

Figure 6 On-Resistance Variation with Temperature



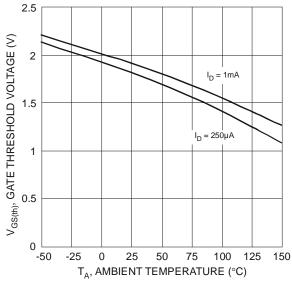
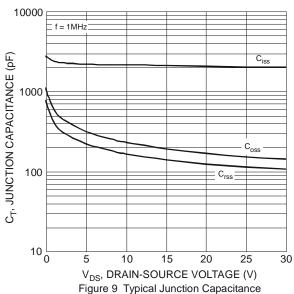
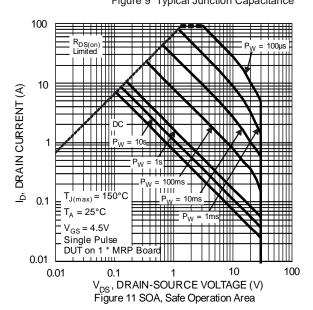
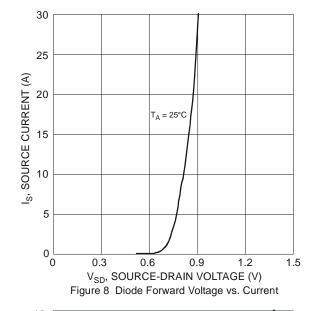
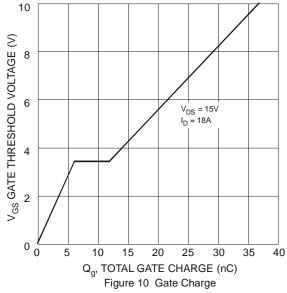


Figure 7 Gate Threshold Variation vs. Ambient Temperature

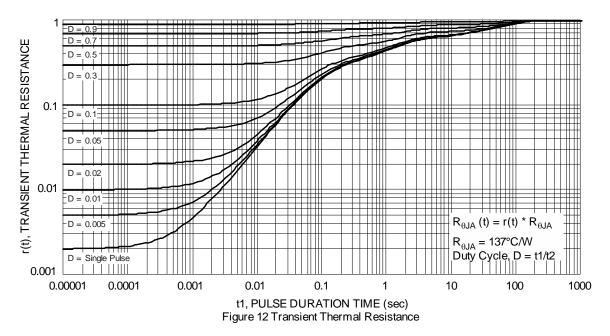








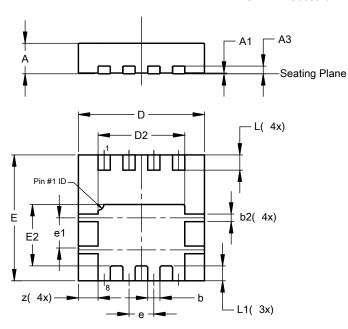




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

POWERDI®3333-8



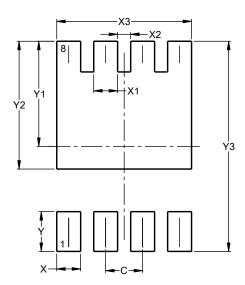
POWERDI®3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	_	_	0.203		
b	0.27	0.37	0.32		
b2	_	_	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
е	-	-	0.65		
e1	0.79	0.89	0.84		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	-	-	0.515		
All Dimensions in mm					



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

POWERDI®3333-8



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700



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